11-14-05

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**PATENT** 

10/649,989

10/64 NOV 09 2005 W

#### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Vladislav Vashchenko, et al.

Appln. No.: 10/649,989

Filed: August 27, 2003

For: SILICON CONTROLLED RECTIFIER

STRUCTURE WITH IMPROVED PUNCH

THROUGH RESISTANCE

Group Art Unit: 2814

Examiner: Long Pham

APPEAL BRIEF

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

This is an appeal from the decision dated May 16, 2005 of the Examiner finally rejecting claim 22.

### Real Party in Interest

The real party in interest is National Semiconductor Corporation as indicated in the assignment recorded at reel 014447, frame 0420-0423, on August 26, 2003.

# Related Appeals and Interferences

Appellant is not aware of any other related appeals or interferences.

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Atty. Docket No. 100-22600 (P05659)

**Appeal Brief** 

## Status of Claims

Claim 22 stands rejected under 35 U.S.C. §102(b) as being anticipated by Sutton (U.S. Patent No. 4,937,647).

Claims 1-4, 6-13, 21, and 23-28 have been allowed.

Claims 5 and 14-20 have been cancelled.

Claim 22 is being appealed.

#### **Status of Amendments**

Appellant's amendment filed on July 14, 2005 was entered into the case.

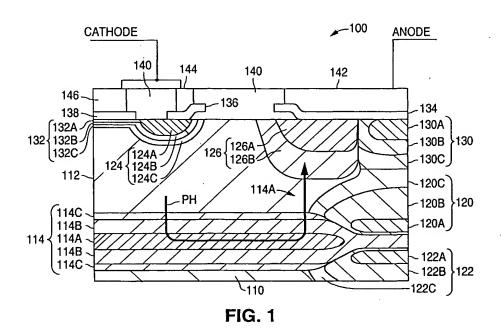
### Summary of Claimed Subject Matter

The subject matter of independent claim 22 is shown in appellant's FIG. 1 (reproduced below), and is a silicon controlled rectifier. The silicon controlled rectifier of claim 22 includes a first semiconductor region of a first conductivity type that has a dopant concentration. (The first semiconductor region can be read to be, for example, n-type epitaxial layer 112 shown in FIG. 1 and discussed on page 2, lines 21-26 of appellant's specification.)

The silicon controlled rectifier also includes a buried region of the first conductivity type. The buried region contacts the first semiconductor region and has a dopant concentration that is greater than the dopant concentration of the first semiconductor region. (The buried region can be read to be, for example, n-type buried layer 114 shown in FIG. 1 and discussed from page 2, line 27 to page 3, line 9 of appellant's specification.)

The silicon controlled rectifier further includes a second semiconductor region of a second conductivity type that contacts the first semiconductor region. The second semiconductor region is spaced apart from the buried region. The second semiconductor region includes all contiguous regions of the second conductivity

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type. (The second semiconductor region can be read to be, for example, p-type region 124 shown in FIG. 1 and discussed on page 4, lines 8-17 of appellant's specification.)

The silicon controlled rectifier additionally includes a third semiconductor region of the first conductivity type that contacts the first semiconductor region. The third semiconductor region is spaced apart from the buried region and the second semiconductor region, and has a dopant concentration that is greater than the dopant concentration of the first semiconductor region. (The third semiconductor region can be read to be, for example, n-type sinker down region 126 shown in FIG. 1 and discussed on page 4, lines 18-24 of appellant's specification.)

# Grounds of Rejection to be Reviewed on Appeal

Claim 22 stands rejected under 35 U.S.C. §102(b) as being anticipated by Sutton (U.S. Patent No. 4,937,647).

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## <u>Argument</u>

Rejection under 35 U.S.C. §102(b) as being anticipated by Sutton (U.S. Patent No. 4,937,647).

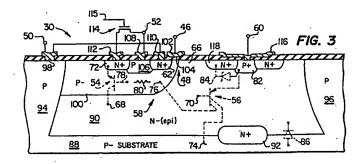
#### Claim 22

Claim 22 recites, in part,

"a buried region of the first conductivity type, the buried region contacting the first semiconductor region and having a dopant concentration that is greater than the dopant concentration of the first semiconductor region;

"a second semiconductor region of a second conductivity type that contacts the first semiconductor region, the second semiconductor region being spaced apart from the buried region, the second semiconductor region including all contiguous regions of the second conductivity type."

In rejecting the claims, the Examiner pointed to n+ buried layer 92 shown in FIG. 3 (reproduced below) of the Sutton reference as constituting the buried region of claim 22, and p-type diffusion 96 shown in FIG. 3 of the Sutton reference as constituting the second semiconductor region of claim 22. P-type diffusion region 96, however, can not be read to be the second semiconductor region required by claim 22.



As noted above, claim 22 requires that the second semiconductor region include all contiguous regions of the second conductivity type. The term "contiguous" in this context means the regions that are in contact and have the second conductivity type. For example, one common usage of the term "contiguous" is with reference to the 48 contiguous states of the United States. Similarly, as shown in FIG. 3 of the Sutton reference, p- substrate 88, p region 94, p region 96, and p- region 100 form a single contiguous region because the regions are in contact and have the same conductivity type.

Thus, even though p- substrate 88 and p region 96 have different dopant concentrations, these two regions form a single contiguous region because both regions are in contact and have the same conductivity type. As a result, p-type diffusion region 96 and p-type substrate 88 must both be read to be a part of the second semiconductor region required by claim 22.

In addition, as further shown in FIG. 3 of the Sutton reference, p-type substrate 88 contacts n+ buried layer 92. Thus, since p-type substrate 88 contacts buried layer 92, and p-type substrate and p-type diffusion 96 must be read together to be a part of the second semiconductor region, the Sutton reference teaches that the second semiconductor region contacts buried layer 92.

However, as noted above, claim 22 requires that the second semiconductor region be spaced apart from the buried region. Thus, since the Sutton reference teaches that the second semiconductor region (which includes substrate 88 and diffusion 96) contacts buried layer 92, the Sutton reference can not anticipate claim 22.

In responding to appellant's argument, the Examiner argued that "the limitation that p-type diffusion region 96 and p-type diffusion region 88 must both be a part of the second semiconductor region is not recited by present claim 22." However, as noted above, claim 22 requires that the second semiconductor region include all contiguous regions of the second conductivity type.

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Thus, in view of the definition of the term "contiguous," claim 22 does require that p-type diffusion region 96 and p-type substrate 88 be read to be a part of the second semiconductor region. Therefore, since the Sutton reference teaches that the second semiconductor region (which includes substrate 88 and diffusion 96) contacts buried layer 92, claim 22 is not anticipated by the Sutton reference.

# Conclusion

The Examiner's rejection is clearly erroneous and should be reversed.

Respectfully submitted,

Dated: \_\_\_\_\_\_\_ E

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#### **CLAIMS APPENDIX**

# 22. A silicon controlled rectifier comprising:

a first semiconductor region of a first conductivity type, the first semiconductor region having a dopant concentration;

a buried region of the first conductivity type, the buried region contacting the first semiconductor region and having a dopant concentration that is greater than the dopant concentration of the first semiconductor region;

a second semiconductor region of a second conductivity type that contacts the first semiconductor region, the second semiconductor region being spaced apart from the buried region, the second semiconductor region including all contiguous regions of the second conductivity type; and

a third semiconductor region of the first conductivity type that contacts the first semiconductor region, the third semiconductor region being spaced apart from the buried region and the second semiconductor region, and having a dopant concentration that is greater than the dopant concentration of the first semiconductor region.

# **EVIDENCE APPENDIX**

The Evidence Appendix is empty.

# **RELATED PROCEEDINGS APPENDIX**

The Related Proceedings Appendix is empty.

Atty. Docket No. 100-22600 (P05659) Approved for use through 07/31/06. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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| TRANSMITTAL FORM  (to be used for all correspondence after initial filing)   |   | Applic                            | ation Number   | 10/649,989  |  |  |  |  |  |  |
|--|---|-----------------------------------|--|---|--|--|--|--|--|--|
|  |   | Filing                            | Date   | August 27, 2003   |  |  |  |  |  |  |
|  |   | First Named Inventor              |  | Vladislav Vashchenko et al.   |  |  |  |  |  |  |
|  |   | Group Art Unit                    |  | 2814  |  |  |  |  |  |  |
|  |   | Exami                             | ner Name   | Long Pham   |  |  |  |  |  |  |
| Total Number of Pages in This Submission 14  |   |                                   | ey Docket Number                                     | 100-22600 (P05659)  |  |  |  |  |  |  |
| ENCLOSURES (check all that apply)  |   |                                   |  |   |  |  |  |  |  |  |
| Fee Transmittal Form (in duplicate)  |   | ment Papers<br>Application)       |  | After Allowance Communication to Group  |  |  |  |  |  |  |
| Fee Attached (\$500)   | ☐ Drawin  | g(s)                              |  | Appeal Brief  |  |  |  |  |  |  |
| ☐ Amendment/Response ☐ Licensi   |   |                                   | d Papers   | Appeal Communication to Group (Appeal Notice, Brief, Reply Brief)   |  |  |  |  |  |  |
| After Final (Response)   |   | Slip (PTO/SB/69)<br>ring Petition | Proprietary Information                              |   |  |  |  |  |  |  |
| Affidavits/declaration(s)  |   | n to Conv<br>onal App             |  | Status Inquiry  |  |  |  |  |  |  |
| Extension of Time Request  |   |                                   | ey, Revocation<br>espondence Address                 | Other Enclosure(s) (please identify below):   |  |  |  |  |  |  |
| Express Abandonment Request Termin   |   |                                   |  | Return Receipt Postcard<br>Express Mail No.<br>EV590185896US  |  |  |  |  |  |  |
| ☐ Information Disclosure Statement ☐ CD, Nu  |   |                                   | CD(s)  |   |  |  |  |  |  |  |
| Certified Copy of Priority Document(s)   |   | rks                               |  | ecessary fees or credit overpayment to 502305. A duplicate copy of this d for this purpose.                         |  |  |  |  |  |  |
| Response to Missing Parts/ Incomplete Application Response to Missing Parts under 37 CFR 1.52 or 1.53              | Triplicate Copies of the Appeal Brief not included in accordance with 37 CFR §41.37(a)(1) |                                   |  |   |  |  |  |  |  |  |
| SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT   |   |                                   |  |   |  |  |  |  |  |  |
| Firm or Individual name  Mark C. Pickering,  |   |                                   | ,  |   |  |  |  |  |  |  |
| Signature WWL C. Films   |   |                                   |  |   |  |  |  |  |  |  |
| Date November 9, 2005  |   |                                   |  |   |  |  |  |  |  |  |
|  | CERTIFIC  | CATEO                             | F EXPRESS MAILING                                    | G   |  |  |  |  |  |  |
| I hereby certify that this correspondence is t<br>EV590185896US in an envelope addressed to:<br>1450 on this date: | peing deposite<br>Mail Stop Ap  | d with the peal Brief-            | United States Postal Se<br>Patents, Commissioner for | rvice with sufficient postage Express Mail No.<br>Patents, P.O. Box 1450, Alexandria, VA 22313.<br>November 9, 2005 |  |  |  |  |  |  |
| Typed or printed name Robin L. King  | (   | , .                               |  |   |  |  |  |  |  |  |
| Signature  | $\forall k \ \forall k$   | 4 4 0                             |  | Data November 9, 2005   |  |  |  |  |  |  |

This collection of information is required by 37 CFR 1.5. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

| OVPE FEE TRANSMITTAL  | T            | Complete if Known                                    |              |           |  |          |  |  |
|---|--------------|--|--------------|-----------|--|----------|--|--|
|   | Appl         | Application Number                                   |              |           | 10/649,989   |          |  |  |
| For FY 2005  NOV 09 2005  Purpose Fees are subject to annual revision.  |              |  |              |           |  |          |  |  |
| NOV 09 2005 Eurent Fees are subject to annual revision.   |              | Filing Date First Named Inventor                     |              |           | August 27, 2003  |          |  |  |
|   |              | Examiner Name  |              |           | Vladislav Vashchenko et al.  |          |  |  |
| press Mail No. EV590185896US  |              | Group Art Unit                                       |              |           | Long Pham  |          |  |  |
| TOTAL AMOUNT OF PAYMENT \$500   |              | Attorney Document No.                                |              |           | 2814   |          |  |  |
| Ψ500  | Attor        | 100 2200 (1 0000)                                    |              |           |  |          |  |  |
| METHOD OF PAYMENT (check one)   | + -          | FEE CALCULATION (continued)                          |              |           |  |          |  |  |
| <ol> <li>The Commissioner is hereby authorized to charge any fees or credi<br/>any overpayment under 37 CFR 1.16 and 1.17 which may be requi</li> </ol> |              | 3. Additional Fees  Large Entity Small Entity        |              |           |  |          |  |  |
| by this paper to Deposit Account No. 502305  LAW OFFICES OF MARK C. PICKERING   | Fee<br>Code  | Fee  |              |           |  |          |  |  |
| ☐ Applicant claims small entity status. See 37 CFR 1.27.  | 1051         | 130  | 2051         | 65        | Surcharge - late filing fee or oath  | T        |  |  |
| 2.   Payment Enclosed:  | 1052         | 50   | 2052         | 25        | Surcharge - late provisional filing fee or                                     |          |  |  |
| ☑ Check ☐ Money Order ☐ Other   |              |  |              | 4.0.0     | cover sheet  |          |  |  |
| FEE CALCULATION   | 1053         | 130  | 1053         | 130       | Non-English specification  |          |  |  |
| 1. FILING FEE/SEARCH FEE/EXAMINATION FEE  | 1812         | 2520   | 1812         | 2520      | For filing a request for ex parte reexamination                                |          |  |  |
| LARGE ENTITY SMALL ENTITY   | 1804         | 920  | 1804         | 920       | Requesting publication of SIR prior to<br>Examiner action                      |          |  |  |
| Fee Code Fee Fee Fee Fee Fee Fee Fee Fee Fee F  |              | 1840   | 1805         | 1840      | Requesting publication of SIR after<br>Examiner action                         |          |  |  |
| 1011/1111/1311 1000 2011/2111/2311 500 Utility<br>1012/1112/1312 430 2012/2112/2312 215 Design  | 1251<br>1252 | 120<br>450   | 2251<br>2252 | 60<br>225 | Extension for reply within first month Extension for reply within second month | -        |  |  |
| 1013/1113/1313 660 2013/2113/2313 330 Plant   | 1253         | 1020   | 2253         | 510       | Extension for reply within second month  |          |  |  |
| 1014/1114/1314 1400 2014/2114/2314 700 Reissue  | 1254         | 1590   | 2254         | 795       | Extension for reply within fourth month  |          |  |  |
| 1005 200 2005 100 Provisional   | 1255         | 2160   | 2255         | 1080      | Extension for reply within fifth month   |          |  |  |
| SUBTOTAL (1) 0  | 1401         | 500  | 2401         | 250       | Notice of Appeal   |          |  |  |
| 2. Extra Claim Fees FOR UTILITY AND REISSUE   | 1402         | 500  | 2402         | 250       | Filing a brief in support of an appeal   | 500      |  |  |
| Extra Fee from<br>Claims below Fee Paid   | 1403         | 1000   | 2403         | 500       | Request for oral hearing   |          |  |  |
| Total Claims $* - 20 ** = 0$ $x 50$ = \$ 0  | 1451         | 1510   | 1451         | 1510      | Petition to institute a public use proceeding                                  |          |  |  |
| Independent $*-3 = 0$ $\times 200 = $0$   | 1452         | 500  | 2452         | 250       | Petition to revive-unavoidable   |          |  |  |
| Multiple Dep. * = \$0   | 1453         | 1500   | 2453         | 750       | Petition to revive-unintentional   | ļ        |  |  |
| ** or number previously paid, if greater; for Reissues, see below:  | 1501         | 1400   | 2501         | 700       | Utility issue fee (or reissue)   |          |  |  |
| Large Entity Small Entity   | 1502         | 800  | 2502         | 400       | Design issue fee   |          |  |  |
| Fee Fee Code Fee (\$) Fee Description Code (\$)   | 1503         | 1100   | 2503         | 550       | Plant issue fee  |          |  |  |
| 1202 50 2202 25 Claim in excess of 20   | 1460         | 1,30   | 1460         | 130       | Petitions to the Commissioner  |          |  |  |
| 1201 200 2201 100 Independent claims in excess of 3   | 1807         | 50   | 1807         | 50        | •  | <u> </u> |  |  |
| 1203 360 2203 180 Multiple dependent claim, if not paid   |              | 180  | 1806         | 180       |  |          |  |  |
| 1204 200 2204 100 ** Reissue ind. claims over original patent   | 8021         | 40   | 8021         | 40        | Recording each patent assignment per<br>property (times number of properties)  |          |  |  |
| 1205 50 2205 25 ** Reissue claims in excess of 20 and over original patent  | 1809         | 790  | 2809         | 395       | Filing a submission after final rejection (37 CFR 1.129(a))                    |          |  |  |
|   | 1810         | 790  | 2810         | 395       | For each additional invention be examined (37 CFR 1.129(b)                     |          |  |  |
|   | 1801         | 790  | 2801         | 395       |  |          |  |  |
|   | 1802         | 900  | 1802         | 900       |  |          |  |  |
| SUBTOTAL (2) \$0  | *Redu        | *Reduced by Basic Filing Fee Paid SUBTOTAL (3) \$500 |              |           |  |          |  |  |
| SUBMITTED BY  |              |  |              |           |  |          |  |  |
| Law Offices of Mark C. Pickering  |              | /  | 1-0          | 3_/       | 5  |          |  |  |
| P.O. Box 300  | Date:        | Date:  |              |           |  |          |  |  |
| Petaluma, CA 94953-0300 Telephone, (707) 762 5583   |              | Date: 11-9-05  |              |           |  |          |  |  |
| Telephone: (707) 762-5583<br>Facsimile: (707) 762-5504  | Bv:          | By: Mark C. Pickering, Reg. No. 36,239               |              |           |  |          |  |  |
| Customer No. 33402  |              |  |              |           |  |          |  |  |
|   |              |  | - ICKCIIII   | o, 10g.   | 10. 50,257   | _        |  |  |